

10V Drive Nch+Pch MOSFET

SH8M70

●Structure

Silicon N-channel / P-channel MOSFET

●Features

- 1) Low on-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (SOP8).

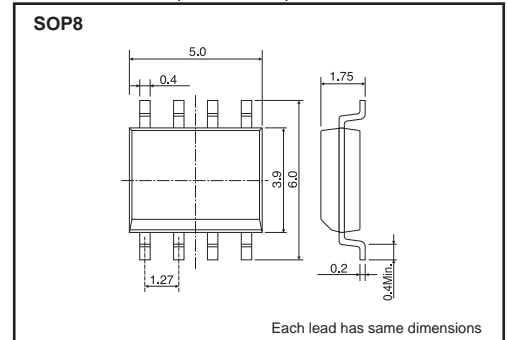
●Application

Power switching, DC / DC converter.

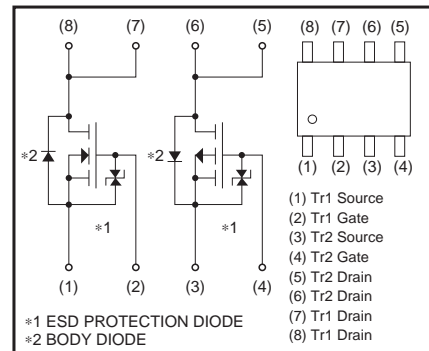
●Packaging specifications

Type	Package	Taping
	Code	TB
	Basic ordering unit (pieces)	2500
SH8M70		○

●Dimensions (Unit : mm)



●Inner circuit



*A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits		Unit
		N-ch	P-ch	
Drain-source voltage	V_{DSS}	250	-250	V
Gate-source voltage	V_{GSS}	30	-20	V
Drain current	Continuous	I_D	± 3.0	A
	Pulsed	I_{DP}^{*1}	± 12	A
Source current (Body diode)	Continuous	I_S	1.0	A
	Pulsed	I_{SP}^{*1}	12	A
Total power dissipation	P_D^{*2}	2.0(TOTAL) 1.4(ELEMENT)		W
Channel temperature	T_{ch}	150		°C
Storage temperature	T_{stg}	-55 to +150		°C

*1 $P_w \leq 10 \mu s$, Duty cycle $\leq 1\%$
*2 MOUNTED ON A CERAMIC BOARD.

N-ch

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	± 10	μA	$V_{GS}=\pm 25V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	250	–	–	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	–	–	25	μA	$V_{DS}=250V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	2.0	–	4.0	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	–	1.25	1.63	Ω	$I_D=1.5A, V_{GS}=10V$
Forward transfer admittance	$ Y_{fs} ^*$	0.75	–	–	S	$I_D=1.5A, V_{DS}=10V$
Input capacitance	C_{iss}	–	180	–	pF	$V_{DS}=25V$
Output capacitance	C_{oss}	–	70	–	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	–	20	–	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}^*$	–	10	–	ns	$I_D=1.5A, V_{DD}\approx 125V$
Rise time	t_r^*	–	20	–	ns	$V_{GS}=10V$
Turn-off delay time	$t_{d(off)}^*$	–	20	–	ns	$R_L=83\Omega$
Fall time	t_f^*	–	25	–	ns	$R_G=10\Omega$
Total gate charge	Q_g^*	–	5.2	–	nC	$V_{DD}\approx 125V$
Gate-source charge	Q_{gs}^*	–	2.1	–	nC	$V_{GS}=10V, I_D=3A$
Gate-drain charge	Q_{gd}^*	–	1.2	–	nC	$R_L=42\Omega, R_G=10\Omega$

*Pulsed

●Body diode characteristics (Source-Drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}^*	–	–	1.5	V	$I_S=3A, V_{GS}=0V$

*Pulsed

P-ch

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	±10	μA	$V_{GS}=\pm 15V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	–250	–	–	V	$I_D=-1mA, V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	–	–	–25	μA	$V_{DS}=-250V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	–2.0	–	–4.0	V	$V_{DS}=-10V, I_D=-1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	–	2.2	2.8	Ω	$I_D=-1.25A, V_{GS}=-10V$
Forward transfer admittance	$ Y_{fs} $ *	1.0	–	–	S	$I_D=-1.25A, V_{DS}=-10V$
Input capacitance	C_{iss}	–	250	–	pF	$V_{DS}=-25V$
Output capacitance	C_{oss}	–	40	–	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	–	10	–	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}$ *	–	9	–	ns	$I_D=-1.25A, V_{DD}=-125V$
Rise time	t_r *	–	15	–	ns	$V_{GS}=-10V$
Turn-off delay time	$t_{d(off)}$ *	–	30	–	ns	$R_L=100\Omega$
Fall time	t_f *	–	20	–	ns	$R_G=10\Omega$
Total gate charge	Q_g *	–	8	–	nC	$V_{DD}=-125V, I_D=-2.5A$
Gate-source charge	Q_{gs} *	–	2.5	–	nC	$V_{GS}=-10V$
Gate-drain charge	Q_{gd} *	–	2.8	–	nC	$R_L=50\Omega, R_G=10\Omega$

*Pulsed

●Body diode characteristics (Source-Drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD} *	–	–	–1.5	V	$I_S=-2.5A, V_{GS}=0V$

*Pulsed

N-ch

●Electrical characteristic curves

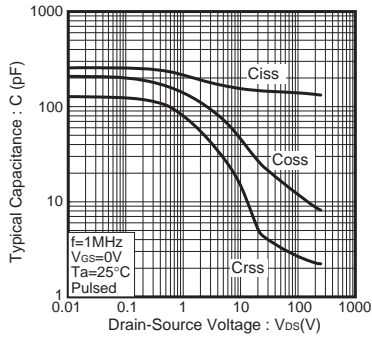


Fig.1 Typical Capacitance vs. Drain-Source Voltage

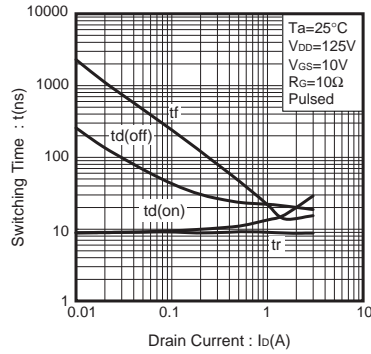


Fig.2 Switching Characteristics

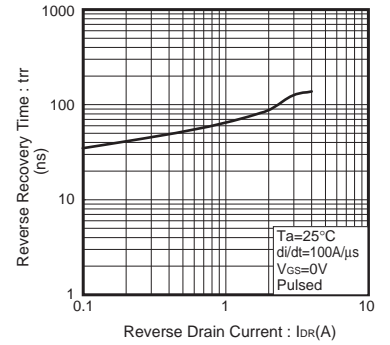


Fig.3 Reverse Recovery Time vs. Reverse Drain Current

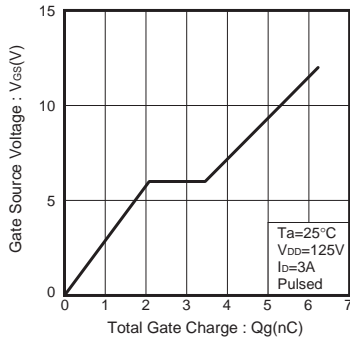


Fig.4 Dynamic Input Characteristics

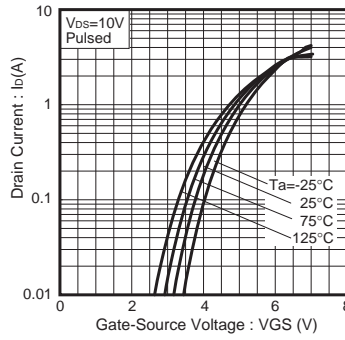


Fig.5 Typical Transfer Characteristics

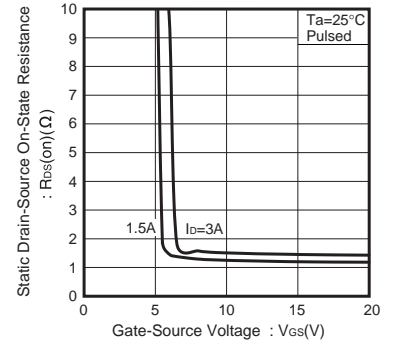


Fig.6 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

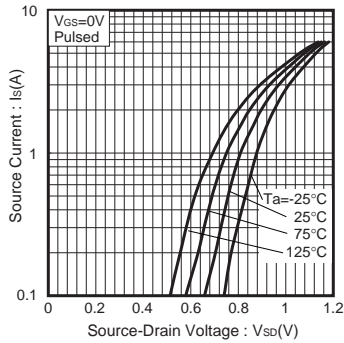


Fig.7 Source Current vs. Source-Drain Voltage

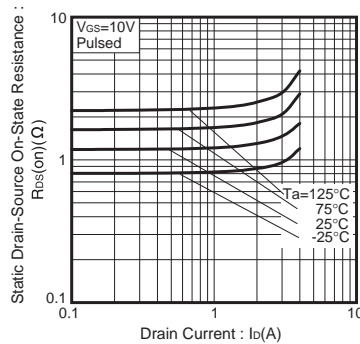


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current

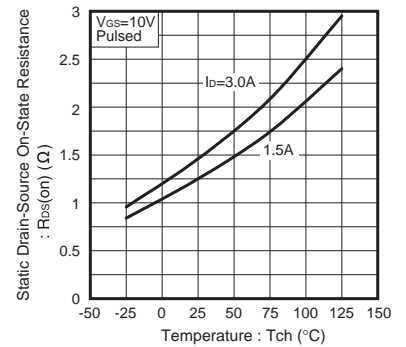


Fig.9 Static Drain-Source On-State Resistance vs. Channel Temperature

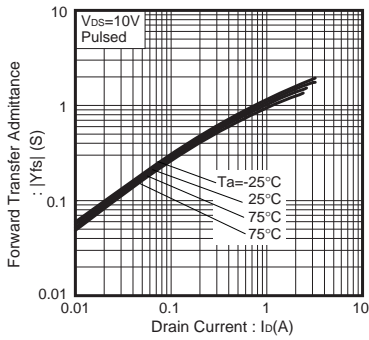


Fig.10 Forward Transfer Admittance vs. Drain Current

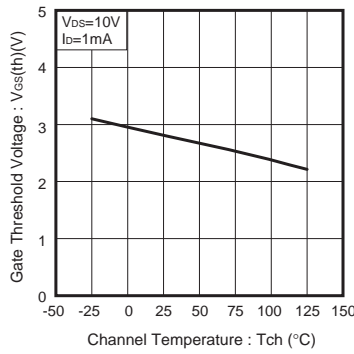


Fig.11 Gate Threshold Voltage vs. Channel Temperature

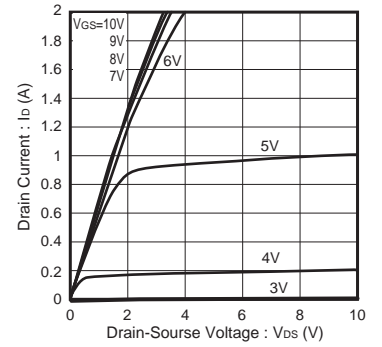


Fig.12 Typical Output Characteristics

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●Electrical characteristic curves

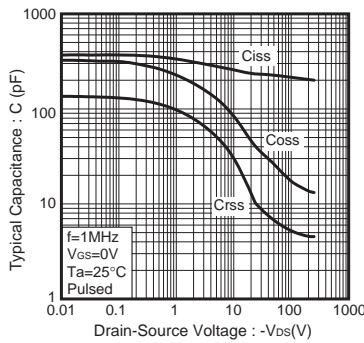


Fig.1 Typical Capacitance vs. Drain-Source Voltage

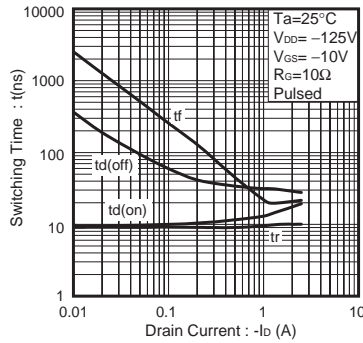


Fig.2 Switching Characteristics

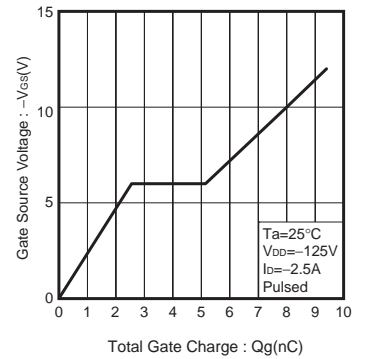


Fig.3 Dynamic Input Characteristics

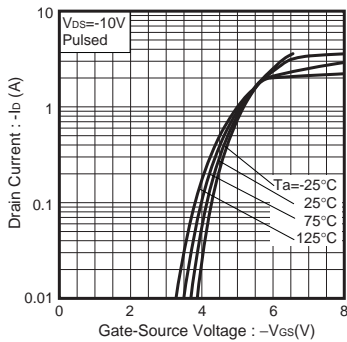


Fig.4 Typical Transfer Characteristics

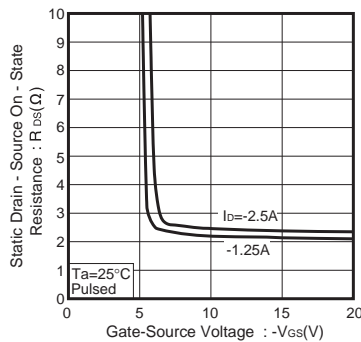


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

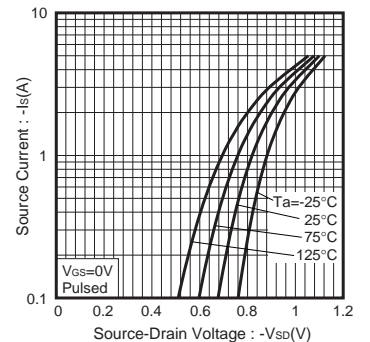


Fig.6 Source Current vs. Source-Drain Voltage

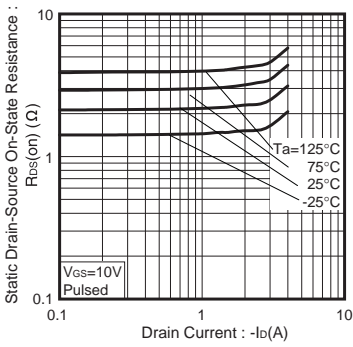


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current

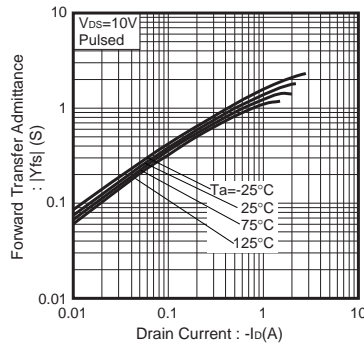


Fig.8 Forward Transfer Admittance vs. Drain Current

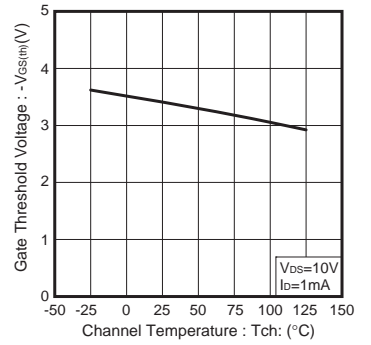


Fig.9 Gate Threshold Voltage vs. Channel Temperature

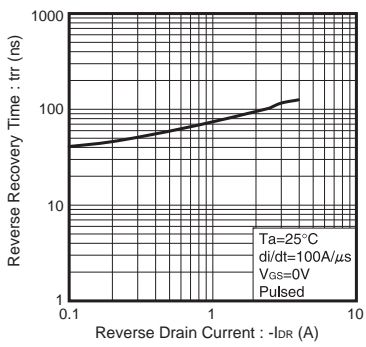


Fig.10 Reverse Recovery Time vs. Reverse Drain Current

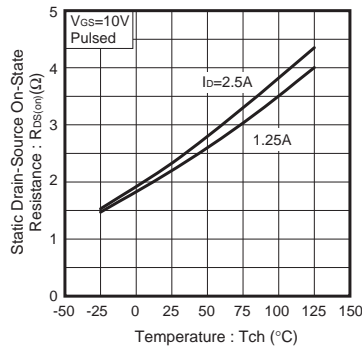


Fig.11 Static Drain-Source On-State Resistance vs. Channel Temperature

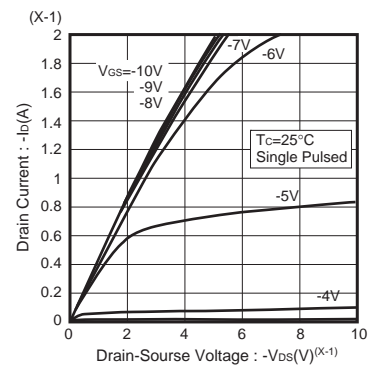


Fig.12 Typical Output Characteristics

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● Measurement circuit

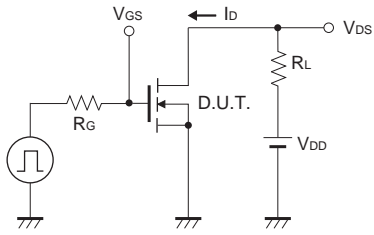


Fig.13 Switching Time Measurement Circuit

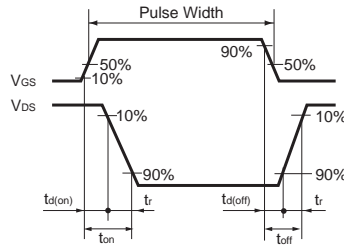


Fig.14 Switching Waveforms

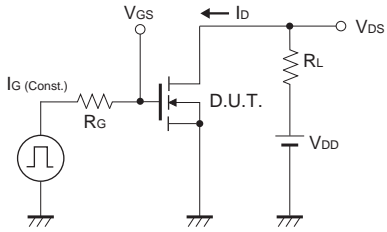


Fig.15 Gate Charge Measurement Circuit

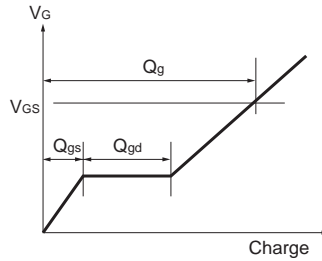


Fig.16 Gate Charge Waveform

P-ch

● Measurement circuit

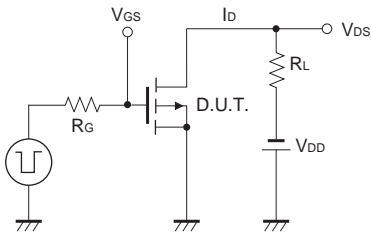


Fig.17 Switching Time Measurement Circuit

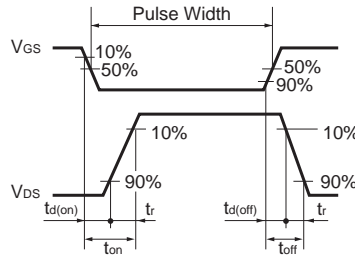


Fig.18 Switching Waveforms

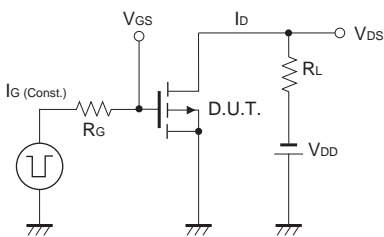


Fig.19 Gate Charge Measurement Circuit

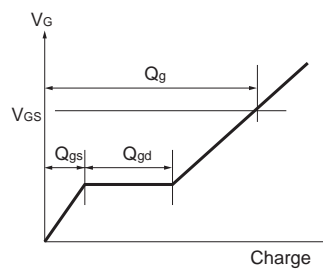


Fig.20 Gate Charge Waveform

Notes

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